

RF Power Field Effect Transistors

High Ruggedness N-Channel Enhancement-Mode Lateral MOSFETs

These high ruggedness devices are designed for use in high VSWR industrial (including laser and plasma exciters), broadcast (analog and digital), aerospace and radio/land mobile applications. They are unmatched input and output designs allowing wide frequency range utilization, between 1.8 and 600 MHz.

- Typical Performance: $V_{DD} = 50$ Volts, $I_{DQ} = 100$ mA

Signal Type	P_{out} (W)	f (MHz)	G_{ps} (dB)	η_D (%)	IRL (dB)
Pulsed (100 μ sec, 20% Duty Cycle)	1250 Peak	230	24.0	74.0	-14
CW	1250 CW	230	22.9	74.6	-15

- Capable of Handling a Load Mismatch of 65:1 VSWR, @ 50 Vdc, 230 MHz, at all Phase Angles, Designed for Enhanced Ruggedness, 1250 Watts Pulsed Peak Power, 20% Duty Cycle, 100 μ sec
- Capable of 1250 Watts CW Operation

Features

- Unmatched Input and Output Allowing Wide Frequency Range Utilization
- Device can be used Single-Ended or in a Push-Pull Configuration
- Qualified Up to a Maximum of 50 V_{DD} Operation
- Characterized from 30 V to 50 V for Extended Power Range
- Suitable for Linear Application with Appropriate Biasing
- Integrated ESD Protection with Greater Negative Gate-Source Voltage Range for Improved Class C Operation
- Characterized with Series Equivalent Large-Signal Impedance Parameters
- RoHS Compliant
- In Tape and Reel. R6 Suffix = 150 Units, 56 mm Tape Width, 13 inch Reel.

Table 1. Maximum Ratings

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	-0.5, +125	Vdc
Gate-Source Voltage	V_{GS}	-6.0, +10	Vdc
Storage Temperature Range	T_{stg}	-65 to +150	°C
Case Operating Temperature	T_C	150	°C
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	1333 6.67	W W/°C
Operating Junction Temperature (1,2)	T_J	225	°C

Table 2. Thermal Characteristics

Characteristic	Symbol	Value (2,3)	Unit
Thermal Resistance, Junction to Case			°C/W
Case Temperature 66°C , 1250 W Pulsed, 100 μ sec Pulse Width, 20% Duty Cycle, 100 mA, 230 MHz	$Z_{\theta JC}$	0.03	
Case Temperature 63°C , 1250 W CW, 100 mA, 230 MHz	$R_{\theta JC}$	0.15	

- Continuous use at maximum temperature will affect MTTF.
- MTTF calculator available at <http://www.freescale.com/rf>. Select Software & Tools/Development Tools/Calculators to access MTTF calculators by product.
- Refer to AN1955, *Thermal Measurement Methodology of RF Power Amplifiers*. Go to <http://www.freescale.com/rf>. Select Documentation/Application Notes - AN1955.

MRFE6VP61K25HR6 MRFE6VP61K25HSR6

**1.8-600 MHz, 1250 W CW, 50 V
LATERAL N-CHANNEL
BROADBAND
RF POWER MOSFETs**

**CASE 375D-05, STYLE 1
NI-1230
MRFE6VP61K25HR6**

**CASE 375E-04, STYLE 1
NI-1230S
MRFE6VP61K25HSR6**

PARTS ARE PUSH-PULL

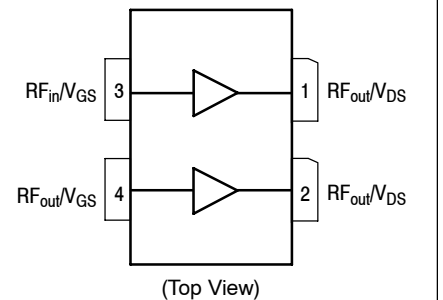


Figure 1. Pin Connections

Table 3. ESD Protection Characteristics

Test Methodology	Class
Human Body Model (per JESD22-A114)	2 (Minimum)
Machine Model (per EIA/JESD22-A115)	B (Minimum)
Charge Device Model (per JESD22-C101)	IV (Minimum)

Table 4. Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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Off Characteristics ⁽¹⁾

Gate-Source Leakage Current ($V_{GS} = 5\text{ Vdc}$, $V_{DS} = 0\text{ Vdc}$)	I_{GSS}	—	—	1	μAdc
Drain-Source Breakdown Voltage ($V_{GS} = 0\text{ Vdc}$, $I_D = 100\text{ mA}$)	$V_{(BR)DSS}$	125	—	—	Vdc
Zero Gate Voltage Drain Leakage Current ($V_{DS} = 50\text{ Vdc}$, $V_{GS} = 0\text{ Vdc}$)	I_{DSS}	—	—	10	μAdc
Zero Gate Voltage Drain Leakage Current ($V_{DS} = 100\text{ Vdc}$, $V_{GS} = 0\text{ Vdc}$)	I_{DSS}	—	—	20	μAdc

On Characteristics

Gate Threshold Voltage ⁽¹⁾ ($V_{DS} = 10\text{ Vdc}$, $I_D = 1776\text{ }\mu\text{Adc}$)	$V_{GS(th)}$	1.7	2.2	2.7	Vdc
Gate Quiescent Voltage ($V_{DD} = 50\text{ Vdc}$, $I_D = 100\text{ mAdc}$, Measured in Functional Test)	$V_{GS(Q)}$	1.4	2.2	2.9	Vdc
Drain-Source On-Voltage ⁽¹⁾ ($V_{GS} = 10\text{ Vdc}$, $I_D = 2\text{ Adc}$)	$V_{DS(on)}$	—	0.15	—	Vdc

Dynamic Characteristics ⁽¹⁾

Reverse Transfer Capacitance ($V_{DS} = 50\text{ Vdc} \pm 30\text{ mV(rms)ac}$ @ 1 MHz, $V_{GS} = 0\text{ Vdc}$)	C_{rss}	—	2.8	—	pF
Output Capacitance ($V_{DS} = 50\text{ Vdc} \pm 30\text{ mV(rms)ac}$ @ 1 MHz, $V_{GS} = 0\text{ Vdc}$)	C_{oss}	—	185	—	pF
Input Capacitance ($V_{DS} = 50\text{ Vdc}$, $V_{GS} = 0\text{ Vdc} \pm 30\text{ mV(rms)ac}$ @ 1 MHz)	C_{iss}	—	562	—	pF

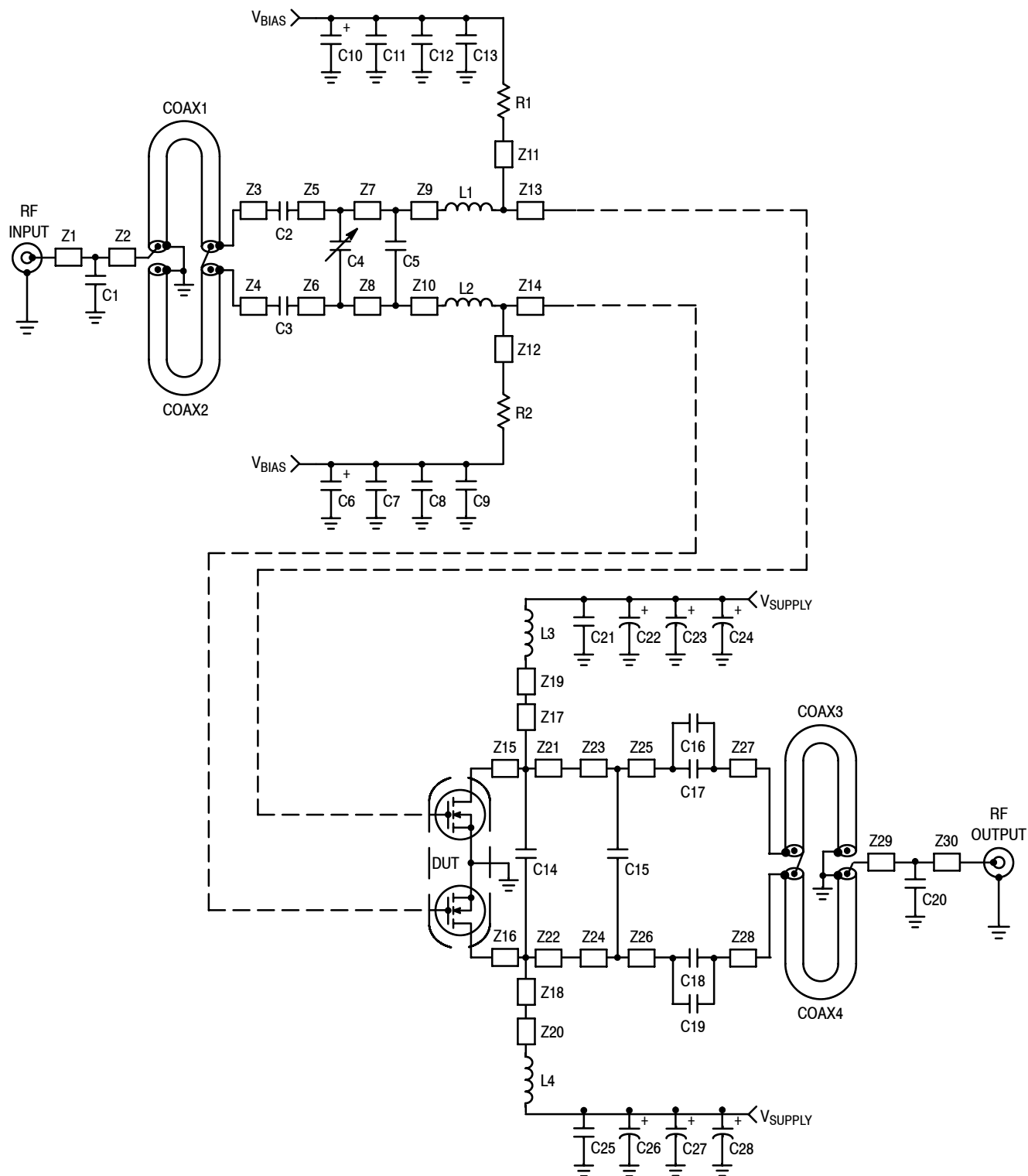
Functional Tests (In Freescale Test Fixture, 50 ohm system) $V_{DD} = 50\text{ Vdc}$, $I_{DQ} = 100\text{ mA}$, $P_{out} = 1250\text{ W Peak}$ (250 W Avg.), $f = 230\text{ MHz}$, Pulsed, 100 μsec Pulse Width, 20% Duty Cycle

Power Gain	G_{ps}	23.0	24.0	26.0	dB
Drain Efficiency	η_D	72.5	74.0	—	%
Input Return Loss	IRL	—	-14	-10	dB

Pulsed RF Performance (In Freescale Application Test Fixture, 50 ohm system) $V_{DD} = 50\text{ Vdc}$, $I_{DQ} = 100\text{ mA}$, $P_{out} = 1250\text{ W Peak}$ (250 W Avg.), $f = 230\text{ MHz}$, Pulsed, 100 μsec Pulse Width, 20% Duty Cycle

Load Mismatch (VSWR 65:1 at all Phase Angles)	Ψ	No Degradation in Output Power			
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1. Each side of device measured separately.



Z1	0.192" x 0.082" Microstrip	Z11*, Z12*	0.872" x 0.058" Microstrip	Z23, Z24	1.251" x 0.300" Microstrip
Z2	0.175" x 0.082" Microstrip	Z13, Z14	0.412" x 0.726" Microstrip	Z25, Z26	0.127" x 0.300" Microstrip
Z3, Z4	0.170" x 0.100" Microstrip	Z15, Z16	0.371" x 0.507" Microstrip	Z27, Z28	0.116" x 0.300" Microstrip
Z5, Z6	0.116" x 0.285" Microstrip	Z17*, Z18*	0.466" x 0.363" Microstrip	Z29	0.186" x 0.082" Microstrip
Z7, Z8	0.116" x 0.285" Microstrip	Z19*, Z20*	1.187" x 0.154" Microstrip	Z30	0.179" x 0.082" Microstrip
Z9, Z10	0.108" x 0.285" Microstrip	Z21, Z22	0.104" x 0.507" Microstrip		

* Line length includes microstrip bends

Figure 2. MRFE6VP61K25HR6(HSR6) Test Circuit Schematic — Pulsed

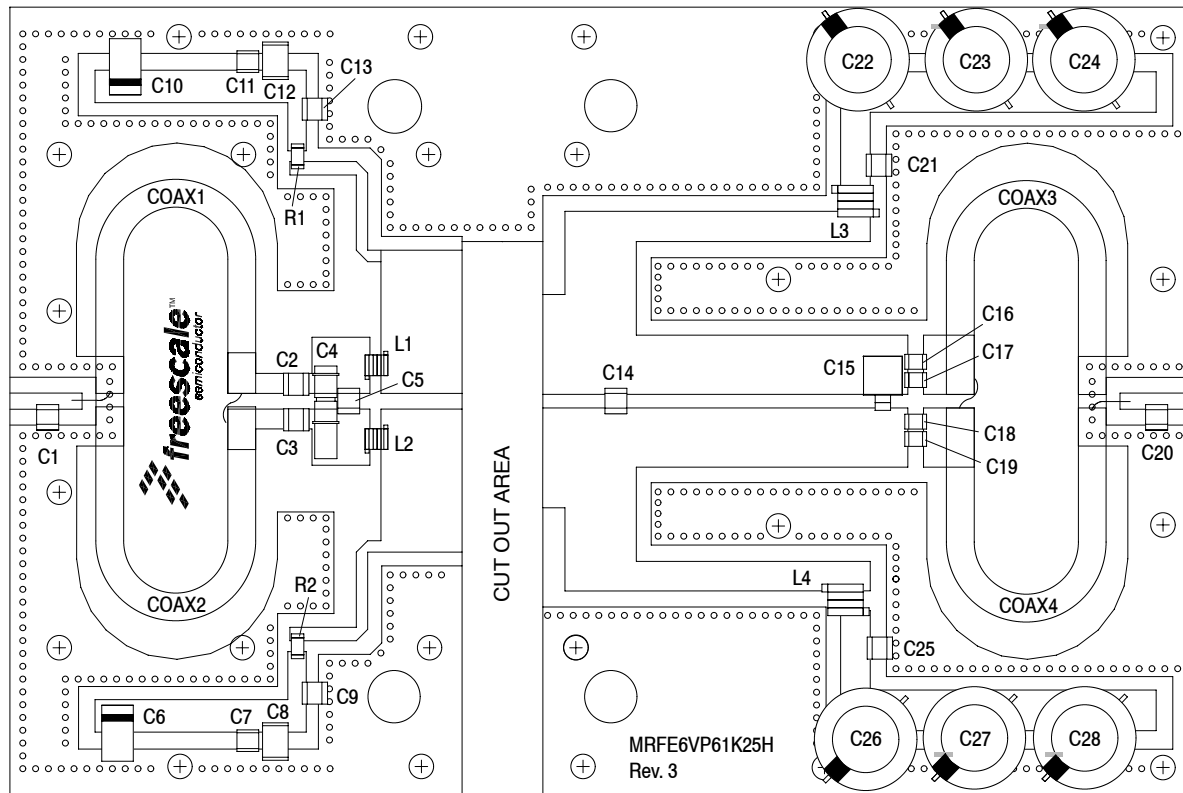
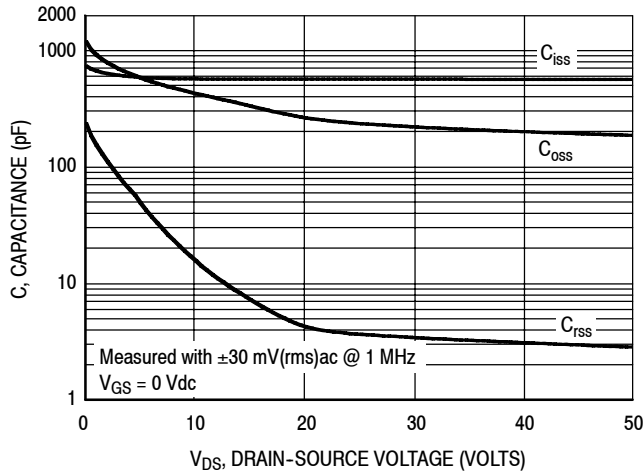


Figure 3. MRFE6VP61K25HR6(HSR6) Test Circuit Component Layout — Pulsed

Table 5. MRFE6VP61K25HR6(HSR6) Test Circuit Component Designations and Values — Pulsed

Part	Description	Part Number	Manufacturer
C1	20 pF Chip Capacitor	ATC100B200JT500XT	ATC
C2, C3, C5	27 pF Chip Capacitors	ATC100B270JT500XT	ATC
C4	0.8–8.0 pF Variable Capacitor, Gigatrim	27291SL	Johanson
C6, C10	22 μ F, 35 V Tantalum Capacitors	T491X226K035AT	Kemet
C7, C11	0.1 μ F Chip Capacitors	CDR33BX104AKYS	AVX
C8, C12	220 nF Chip Capacitors	C1812C224K5RACTU	Kemet
C9, C13, C21, C25	1000 pF Chip Capacitors	ATC100B102JT50XT	ATC
C14	43 pF Chip Capacitor	ATC100B430JT500XT	ATC
C15	75 pF Metal Mica	MIN02-002EC750J-F	CDE
C16, C17, C18, C19	240 pF Chip Capacitors	ATC100B241JT200XT	ATC
C20	6.2 pF Chip Capacitor	ATC100B6R2BT500XT	ATC
C22, C23, C24, C26, C27, C28	470 μ F, 63 V Electrolytic Capacitors	MCGPR63V477M13X26-RH	Multicomp
Coax1, 2, 3, 4	25 Ω Semi Rigid Coax, 2.2" Long	UT-141C-25	Micro-Coax
L1, L2	5 nH Inductors	A02TKLC	Coilcraft
L3, L4	6.6 nH Inductors	GA3093-ALC	Coilcraft
R1, R2	10 Ω Chip Resistors	CRCW120610R0JNEA	Vishay
PCB	0.030", $\epsilon_r = 2.55$	AD255A	Arlon

TYPICAL CHARACTERISTICS



Note: Each side of device measured separately.

Figure 4. Capacitance versus Drain-Source Voltage

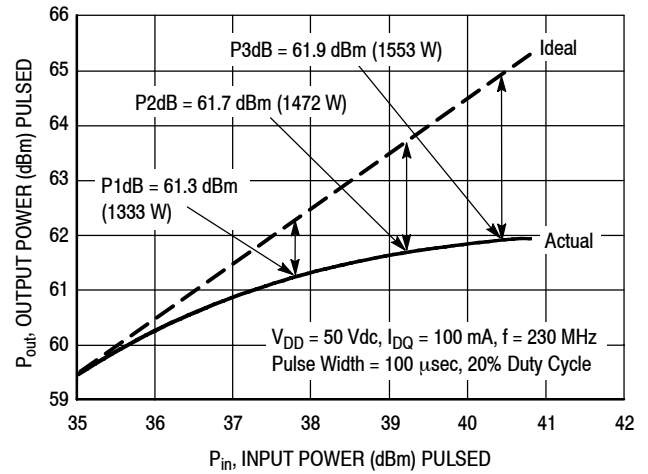


Figure 5. Pulsed Output Power versus Input Power

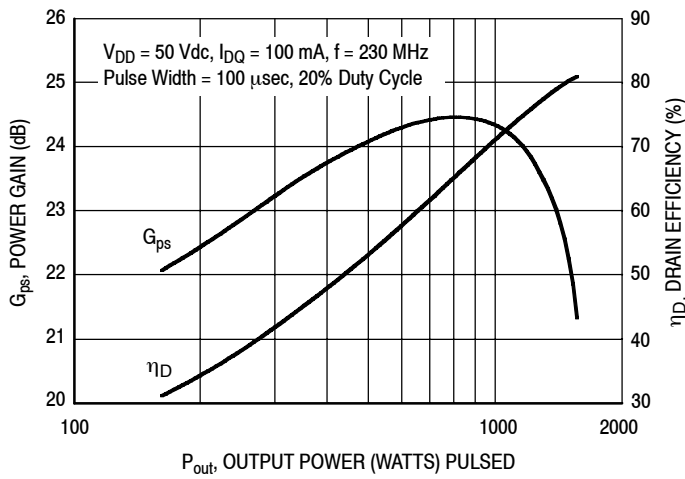


Figure 6. Pulsed Power Gain and Drain Efficiency versus Output Power

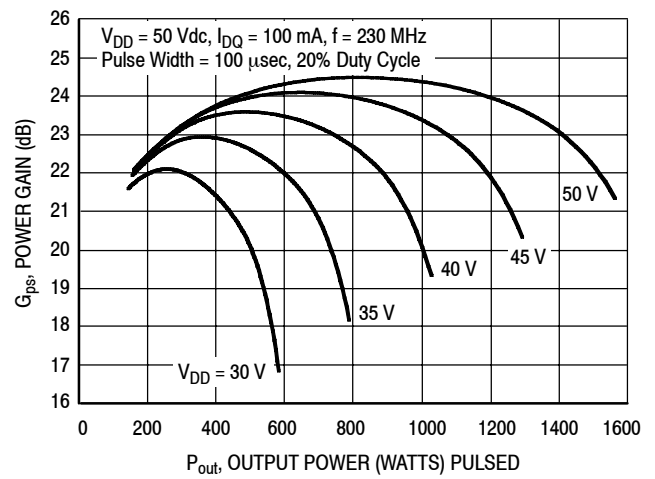


Figure 7. Pulsed Power Gain versus Output Power

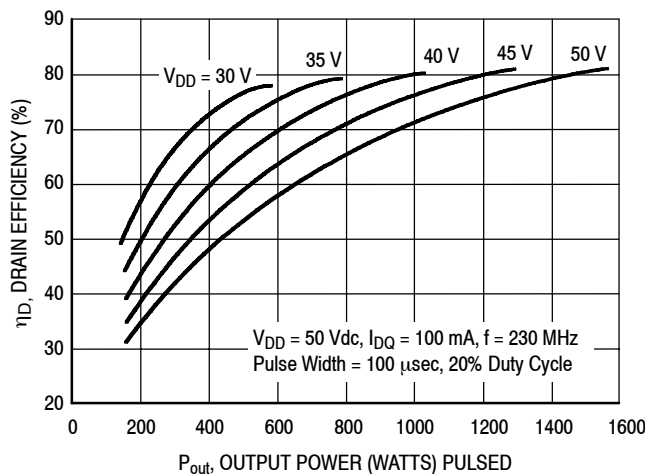


Figure 8. Pulsed Drain Efficiency versus Output Power

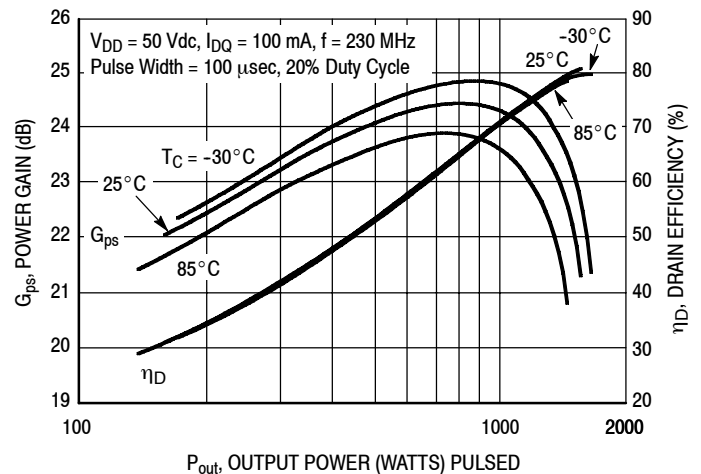
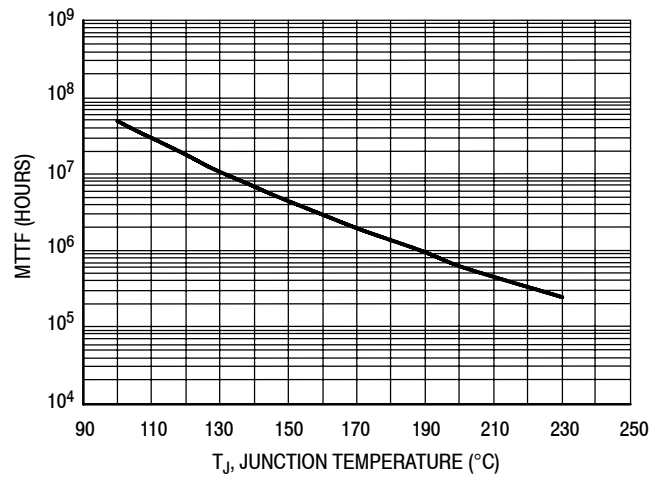


Figure 9. Pulsed Power Gain and Drain Efficiency versus Output Power

MRFE6VP61K25HR6 MRFE6VP61K25HSR6

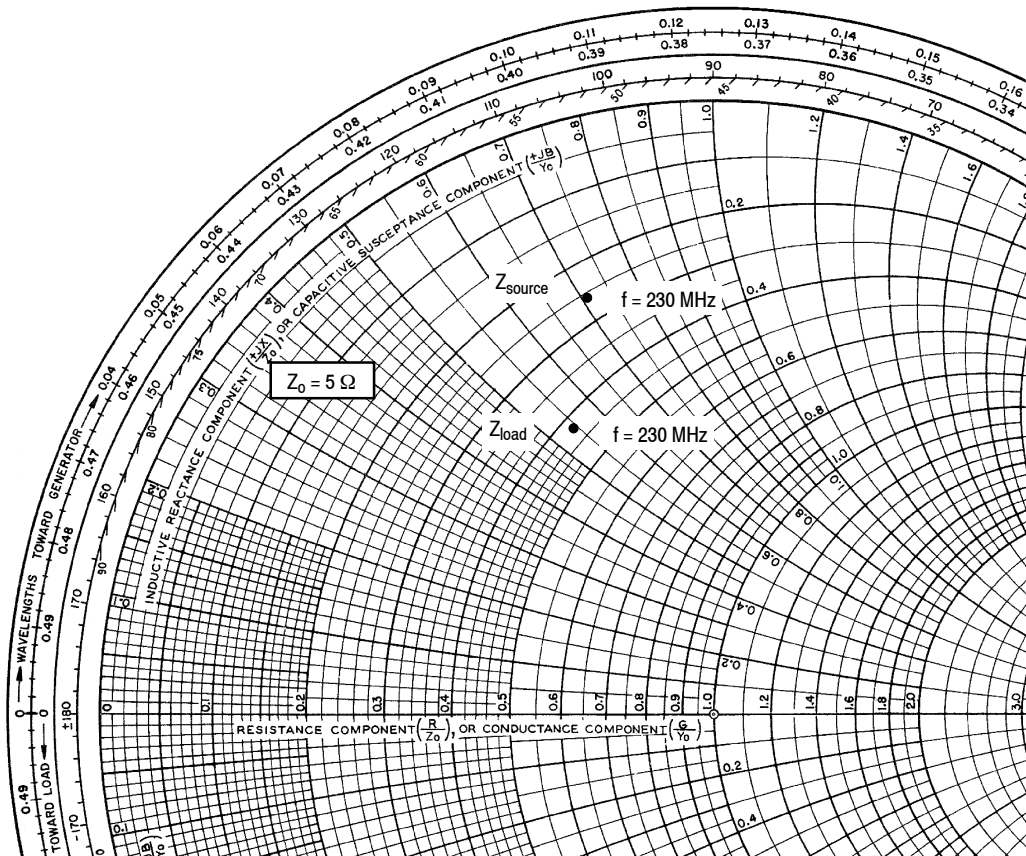
TYPICAL CHARACTERISTICS



This above graph displays calculated MTTF in hours when the device is operated at $V_{DD} = 50$ Vdc, $P_{out} = 1250$ W CW, and $\eta_D = 74.6\%$.

MTTF calculator available at <http://www.freescale.com/rf>. Select Software & Tools/Development Tools/Calculators to access MTTF calculators by product.

Figure 10. MTTF versus Junction Temperature — CW



$V_{\text{DD}} = 50 \text{ Vdc}$, $I_{\text{DQ}} = 100 \text{ mA}$, $P_{\text{out}} = 1250 \text{ W Peak}$

f MHz	Z_{source} Ω	Z_{load} Ω
230	$1.29 + j3.54$	$2.12 + j2.68$

Z_{source} = Test circuit impedance as measured from gate to gate, balanced configuration.

Z_{load} = Test circuit impedance as measured from drain to drain, balanced configuration.

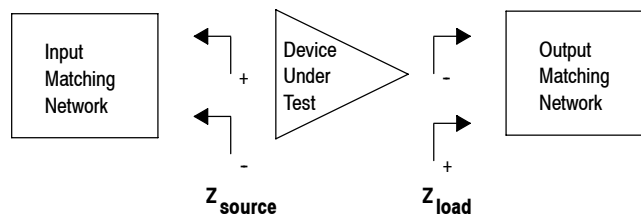
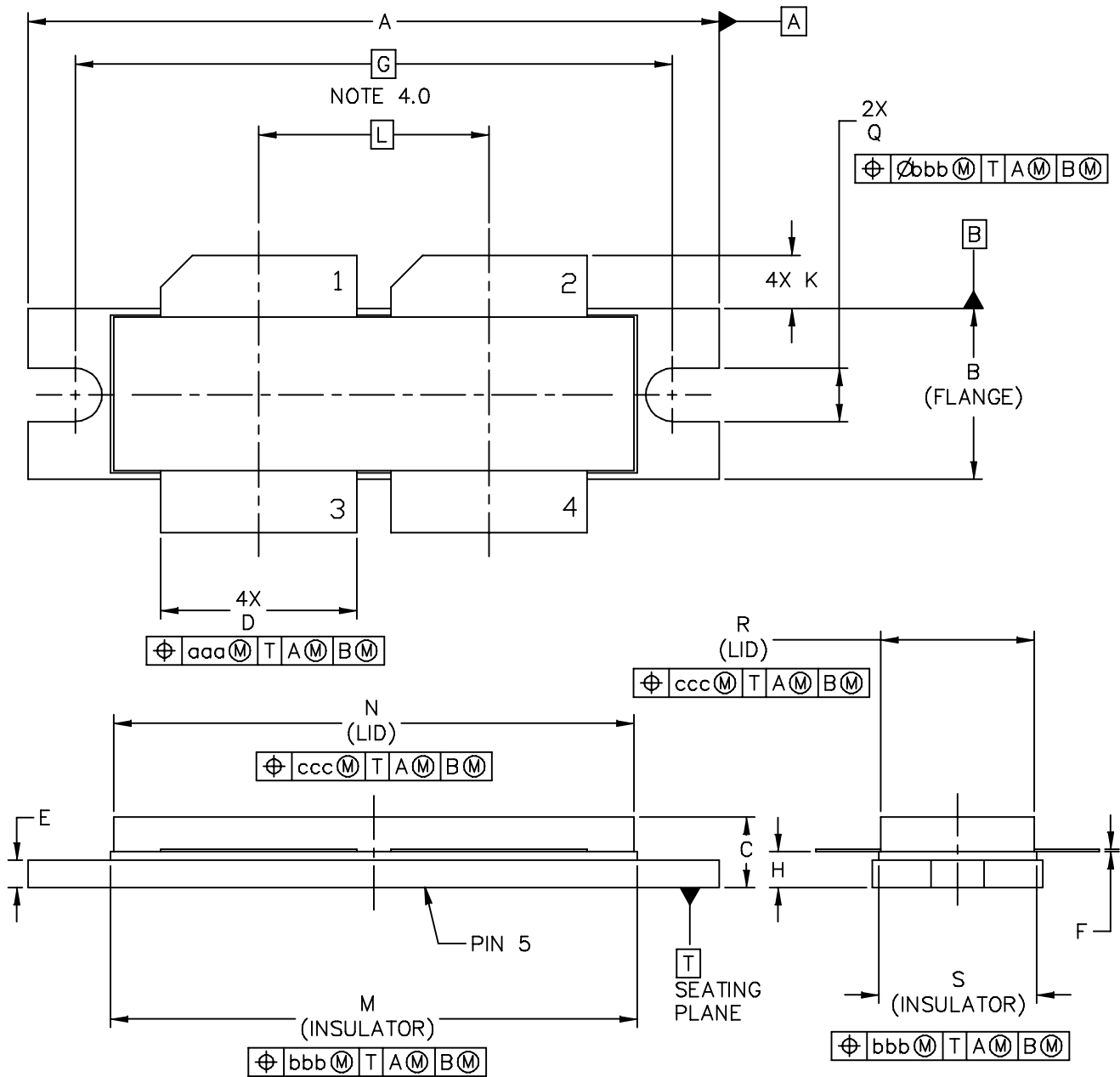


Figure 11. Series Equivalent Source and Load Impedance

PACKAGE DIMENSIONS



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TITLE: NI-1230		DOCUMENT NO: 98ASB16977C	REV: E
		CASE NUMBER: 375D-05	31 MAR 2005
		STANDARD: NON-JEDEC	

NOTES:

- 1.0 INTERPRET DIMENSIONS AND TOLERANCES
PER ASME Y14.5M-1994.
- 2.0 CONTROLLING DIMENSION: INCH
- 3.0 DIMENSION H IS MEASURED .030 (0.762)
AWAY FROM PACKAGE BODY.
- 4.0 RECOMMENDED BOLT CENTER DIMENSION OF
1.52 (38.61) BASED ON M3 SCREW.

STYLE 1:

- PIN 1 - DRAIN
2 - DRAIN
3 - GATE
4 - GATE
5 - SOURCE

INCH			MILLIMETER		INCH			MILLIMETER	
DIM	MIN	MAX	MIN	MAX	DIM	MIN	MAX	MIN	MAX
A	1.615	1.625	41.02	41.28	N	1.218	1.242	30.94	31.55
B	.395	.405	10.03	10.29	Q	.120	.130	3.05	3.3
C	.150	.200	3.81	5.08	R	.355	.365	9.01	9.27
D	.455	.465	11.56	11.81	S	.365	.375	9.27	9.53
E	.062	.066	1.57	1.68					
F	.004	.007	0.1	0.18					
G	1.400 BSC		35.56 BSC		aaa	.013		0.33	
H	.082	.090	2.08	2.29	bbb	.010		0.25	
K	.117	.137	2.97	3.48	ccc	.020		0.51	
L	.540 BSC		13.72 BSC						
M	1.219	1.241	30.96	31.52					
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TITLE: NI-1230					DOCUMENT NO: 98ASB16977C			REV: E	
					CASE NUMBER: 375D-05			31 MAR 2005	
					STANDARD: NON-JEDEC				

NOTES:

1. INTERPRET DIMENSIONS AND TOLERANCES
PER ASME Y14.5M-1994.

2. CONTROLLING DIMENSION: INCH

3. DIMENSION H IS MEASURED .030
AWAY FROM PACKAGE BODY

STYLE 1:

PIN 1 - DRAIN
2 - DRAIN
3 - GATE
4 - GATE
5 - SOURCE

DIM	INCHES		MILLIMETERS		DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX		MIN	MAX	MIN	MAX
A	1.265	1.275	32.13	32.38	R	.355	.365	9.01	9.27
B	.395	.405	10.03	10.29	S	.365	.375	9.27	9.53
C	.150	.200	3.81	5.08	Z	---	.040	---	1.02
D	.455	.465	11.56	11.81					
E	.062	.066	1.57	1.68	aaa	.013		0.33	
F	.004	.007	0.1	0.18	bbb	.010		0.25	
H	.082	.090	2.08	2.29	ccc	.020		0.51	
K	.117	.137	2.97	3.48					
L	.540 BSC		13.72 BSC						
M	1.219	1.241	30.96	31.52					
N	1.218	1.242	30.94	31.55					
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					CASE NUMBER: 375E-04				05 AUG 2005
					STANDARD: NON-JEDEC				

PRODUCT DOCUMENTATION AND SOFTWARE

Refer to the following documents and software to aid your design process.

Application Notes

- AN1955: Thermal Measurement Methodology of RF Power Amplifiers

Engineering Bulletins

- EB212: Using Data Sheet Impedances for RF LDMOS Devices

Software

- Electromigration MTTF Calculator
- RF High Power Model
- .s2p File

For Software, do a Part Number search at <http://www.freescale.com>, and select the “Part Number” link. Go to the Software & Tools tab on the part’s Product Summary page to download the respective tool.

REVISION HISTORY

The following table summarizes revisions to this document.

Revision	Date	Description
0	Nov. 2010	• Initial Release of Data Sheet

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